

T-67-2155

**KS54HCTLs 239
KS74HCTLs****Dual 1-of-4 Decoders/Demultiplexers****FEATURES**

- Designed specifically for high-speed memory decoders and data transmission systems
- Incorporates 2 enable inputs to simplify cascading and/or data reception
- Function, pin-out, speed and drive compatibility with 54/74LS logic family
- Low power consumption characteristic of CMOS
- High-Drive-Current outputs:
 $I_{OL} = 8 \text{ mA} @ V_{OL} = 0.5V$
- Inputs and outputs interface directly with TTL, NMOS and CMOS devices
- Wide operating voltage range: 4.5V to 5.5V
- Characterized for operation over industrial and military temperature ranges:
KS74HCTLs: -40°C to $+85^{\circ}\text{C}$
KS54HCTLs: -55°C to $+125^{\circ}\text{C}$
- Package options include plastic "small outline" packages, standard plastic and ceramic 300-mil DIPs

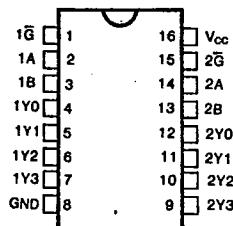
DESCRIPTION

These devices are designed to be used in high-performance memory-decoding or data-routing applications requiring very short propagation delay times. In high-performance memory systems, these decoders can be used to minimize the effects of system decoding. When used with high-speed memories utilizing a fast-enable circuit, the delay times of these decoders and the enable time of the memory are usually less than the typical access time of the memory.

This means that the effective system delay introduced by the decoder is negligible.

These devices provide speeds and drive capability equivalent to their LSTTL counterparts and yet maintain CMOS power levels. The input and output voltage levels allow direct interface with TTL, NMOS and CMOS devices without any external components.

All inputs and outputs are protected from damage due to static discharge by internal diode clamps to Vcc and ground.

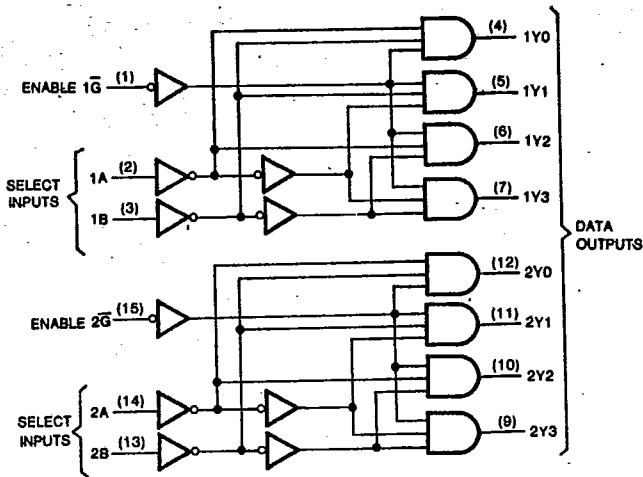
PIN CONFIGURATION**FUNCTION TABLE**

Enable	Inputs		Outputs			
	\bar{G}	Select	Y0	Y1	Y2	Y3
B	A	X	X	L	L	L
H	X	L	H	L	L	L
L	L	H	L	H	L	L
L	H	L	L	L	H	L
L	H	H	L	L	L	H



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LOGIC DIAGRAM



Absolute Maximum Ratings*

Supply Voltage Range V _{CC}	-0.5V to +7V
DC Input Diode Current, I _{IK}		
(V _I < -0.5V or V _I > V _{CC} + 0.5V)	±20 mA
DC Output Diode Current, I _{OK}		
(V _O < -0.5V or V _O > V _{CC} + 0.5V)	±20 mA
Continuous Output Current Per Pin, I _O		
(-0.5V < V _O < V _{CC} + 0.5V)	±70 mA
Continuous Current Through		
V _{CC} or GND pins	±250 mA
Storage Temperature Range, T _{STG}	-65°C to +150°C
Power Dissipation Per Package, P _{D†}	500 mW

† Power Dissipation temperature derating:
Plastic Package (N): -12mW/ $^{\circ}$ C from 65 $^{\circ}$ C to 85 $^{\circ}$ C
Ceramic Package (J): -12mW/ $^{\circ}$ C from 100 $^{\circ}$ C to 125 $^{\circ}$ C

Recommended Operating Conditions

Supply Voltage, V _{CC}	4.5V to 5.5V
DC Input & Output Voltages*, V _{IN} , V _{OUT}	0V to V _{CC}
Operating Temperature	
Range	KS74HCTLs: -40°C to +85°C
	KS54HCTLs: -55°C to +125°C
Input Rise & Fall Times, t _R , t _F	Max 500 ns
* Unused inputs must always be tied to an appropriate logic voltage level (either V _{CC} or GND)	



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KS54HCTLs 239
KS74HCTLsDual 1-of-4 Decoders/Demultiplexers
T-67-21-55DC ELECTRICAL CHARACTERISTICS (V_{CC}=5V±10% Unless Otherwise Specified)

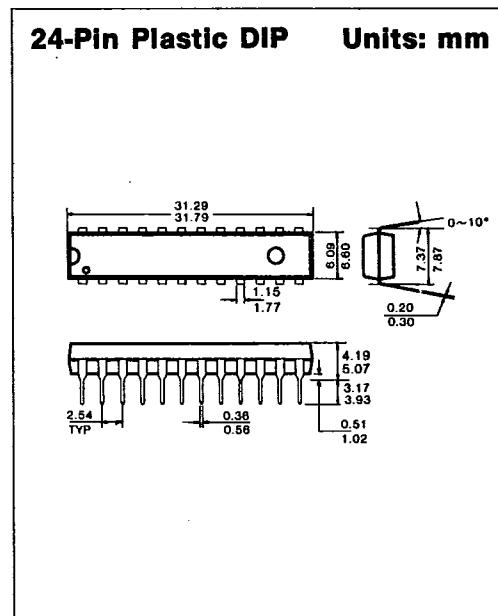
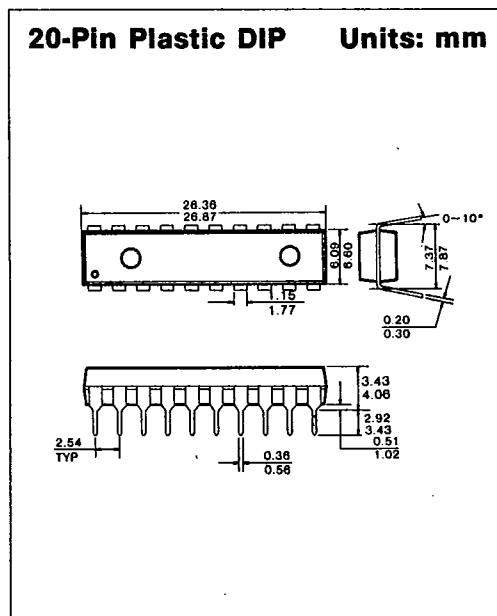
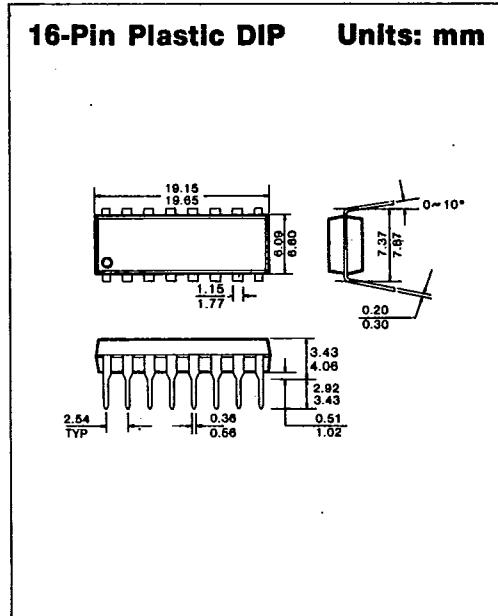
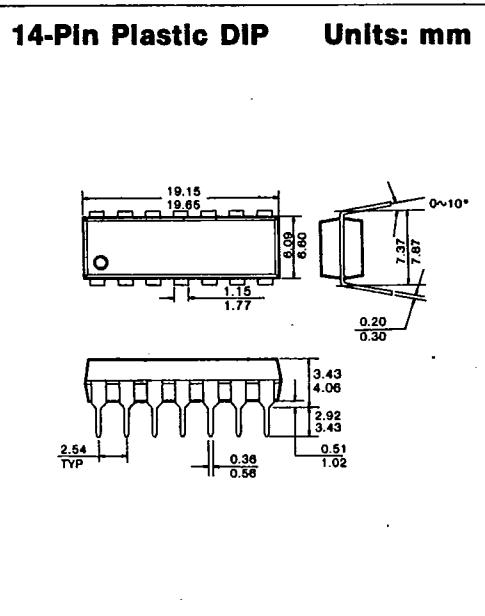
Characteristic	Symbol	Test Conditions	T _A =25°C	KS74HCTLs	KS54HCTLs	Unit
			Typ	Guaranteed Limits		
Minimum High-Level Input Voltage	V _H		2.0	2.0	.2.0	V
Maximum Low-Level Input Voltage	V _L		0.8	0.8	0.8	V
Minimum High-Level Output Voltage	V _{OH}	V _{IN} =V _H or V _L I _O =-20μA I _O =-4mA	V _{CC} 4.2	V _{CC} -0.1 3.98	V _{CC} -0.1 3.84	V _{CC} -0.1 3.7
Maximum Low-Level Output Voltage	V _{OL}	V _{IN} =V _H or V _L I _O =20μA I _O =4mA I _O =8mA	0	0.1 0.26 0.39	0.1 0.33 0.5	0.1 0.4
Maximum Input Current	I _{IN}	V _{IN} =V _{CC} or GND		±0.1	±1.0	μA
Maximum Quiescent Supply Current	I _{CC}	V _{IN} =V _{CC} or GND I _{OUT} =0μA		8.0	80.0	160.0
Additional Worst Case Supply Current	ΔI _{CC}	per input pin V _I =2.4V other Inputs: at V _{CC} or GND I _{OUT} =0μA		2.7	2.9	3.0

AC ELECTRICAL CHARACTERISTICS (Input t_r, t_f≤6 ns), HCTLs239

Characteristic	Symbol	Conditions ^t	T _A =25°C	KS74HCTLs	KS54HCTLs	Unit
			V _{CC} =5.0V	T _A =-40°C to +85°C V _{CC} =5.0V±10%	T _A =-55°C to +125°C V _{CC} =5.0V±10%	
		Typ	Guaranteed Limits			
Maximum Propagation Delay, A or B any Y	t _{PLH}	C _L =50pF	22	30	37	45
	t _{PHL}		22	30	37	45
Maximum Propagation Delay, G to any Y	t _{PLH}	C _L =50pF	21	8	35	42
	t _{PHL}		22	8	35	42
Maximum Input Capacitance	C _{IN}		5			pF
Power Dissipation Capacitance*	C _{PD}		50			pF

* C_{PD} determines the no-load dynamic power dissipation: P_D=C_{PD} V_{CC}² f + I_{CC} V_{CC}.^t For AC switching test circuits and timing waveforms see section 2.

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PACKAGE DIMENSIONST-90-20**1. PLASTIC PACKAGES**

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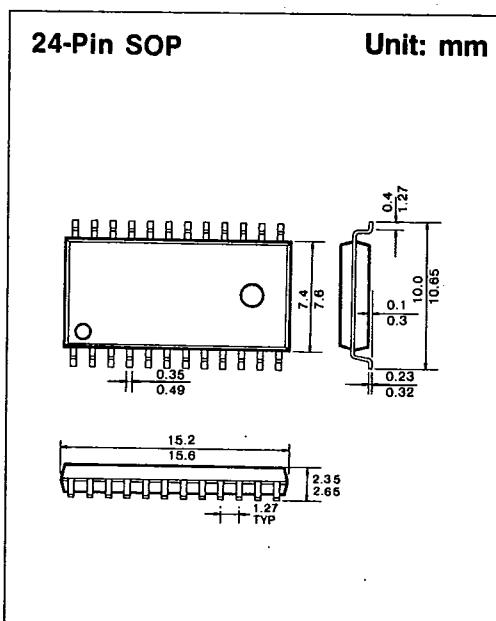
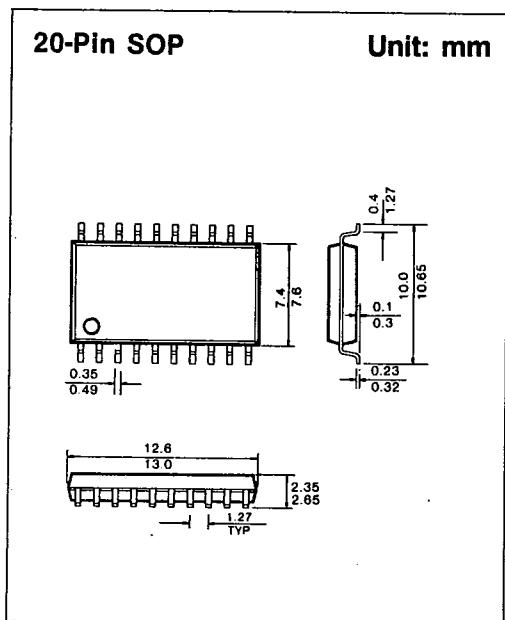
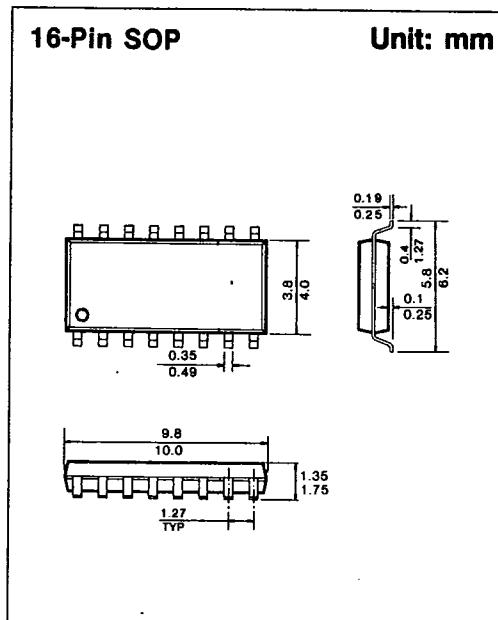
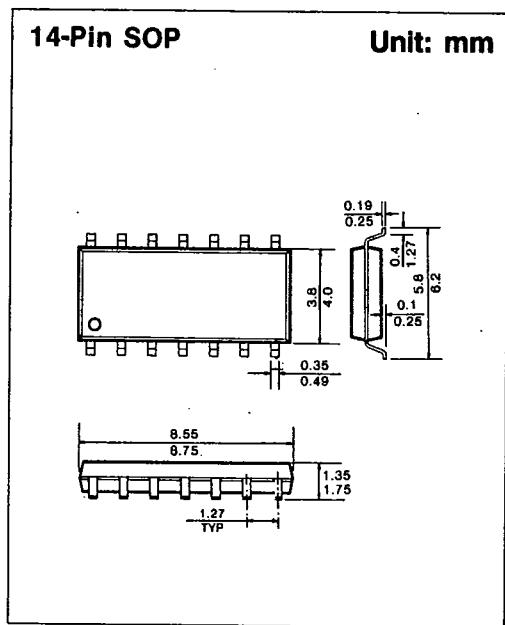


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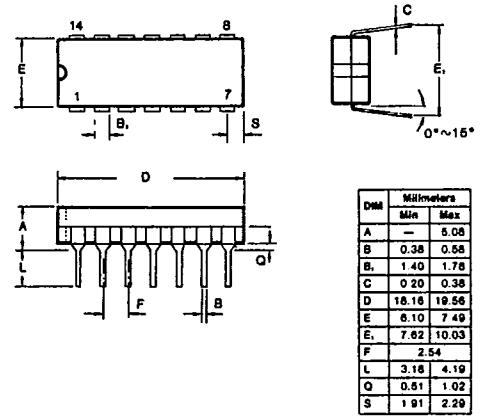
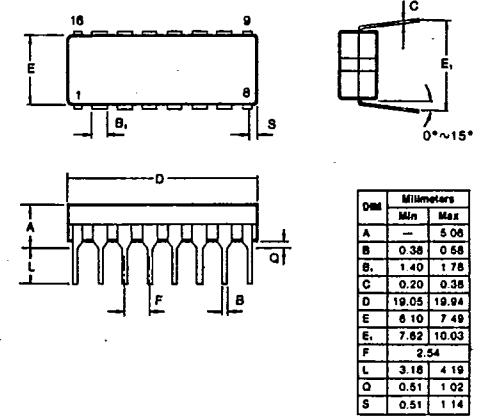
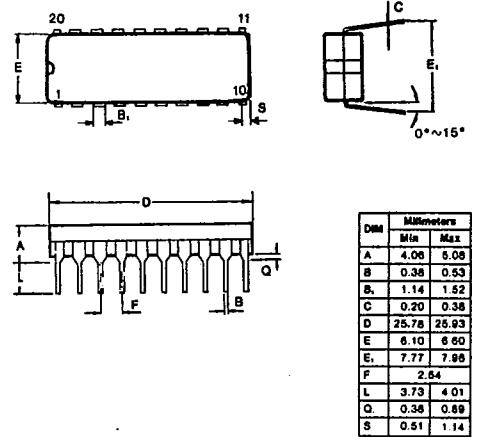
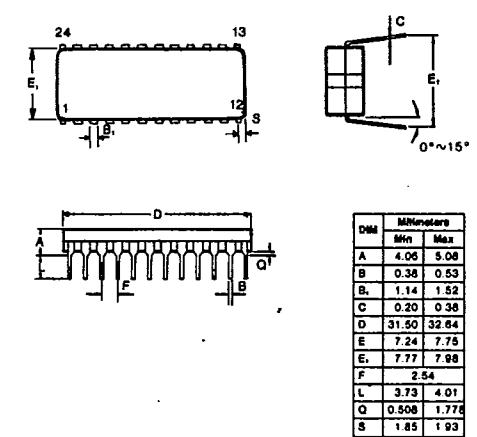
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PACKAGE DIMENSIONS**T-90-20****SAMSUNG SEMICONDUCTOR****1676****A-05**

782

PACKAGE DIMENSIONST-90-20**2. CERAMIC PACKAGES****14-Pin Ceramic DIP Units: mm****16-Pin Ceramic DIP Units: mm****20-Pin Ceramic DIP Units: mm****24-Pin Ceramic DIP Units: mm**

7



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783